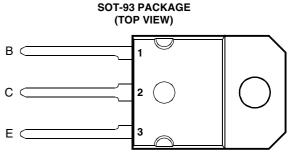
# TIP3055 NPN SILICON POWER TRANSISTOR

# BOURNS®

- Designed for Complementary Use with the TIP2955 Series
- 90 W at 25°C Case Temperature
- 15 A Continuous Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

#### absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT	
Collector-base voltage $(I_E = 0)$	V <sub>CBO</sub>	100	V	
Collector-emitter voltage (I <sub>B</sub> = 0) (see Note 1)	V <sub>CER</sub>	70	V	
Emitter-base voltage	V <sub>EBO</sub>	7	V	
Continuous collector current	Ι <sub>C</sub>	15	A	
Continuous base current	Ι <sub>Β</sub>	7	A	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)	P <sub>tot</sub>	90	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)	P <sub>tot</sub>	3.5	W	
Unclamped inductive load energy (see Note 4)	½Ll <sub>C</sub> ²	62.5	mJ	
Operating junction temperature range	Т <sub>і</sub>	-65 to +150	°C	
Storage temperature range	T <sub>stg</sub>	-65 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds	TL	260	°C	

NOTES: 1. This value applies when the base-emitter resistance  $R_{BE} = 100 \Omega$ .

2. Derate linearly to 150°C case temperature at the rate of 0.72 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH,  $I_{B(on)} = 0.4$  A,  $R_{BE} = 100 \Omega$ ,  $V_{BE(off)} = 0$ ,  $R_S = 0.1 \Omega$ ,  $V_{CC} = 10$  V.

## PRODUCT INFORMATION



#### electrical characteristics at 25°C case temperature

PARAMETER			TEST CONDITIO	NS	MIN	ТҮР	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> = 30 mA	I <sub>B</sub> = 0	(see Note 5)	60			V
I <sub>CER</sub>	Collector-emitter cut-off current	V <sub>CE</sub> = 70 V	R <sub>BE</sub> = 100 Ω				1	mA
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> = 30 V	l <sub>B</sub> = 0				0.7	mA
I <sub>CEV</sub>	Voltage between base and emitter	V <sub>CE</sub> = 100 V	V <sub>BE</sub> = -1.5 V				5	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> = 7 V	I <sub>C</sub> = 0				5	mA
h <sub>FE</sub>	Forward current transfer ratio	$V_{CE} = 4 V$ $V_{CE} = 4 V$	$I_{\rm C} = 4A$ $I_{\rm C} = 10A$	(see Notes 5 and 6)	20 5		70	
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>B</sub> = 0.4 A I <sub>B</sub> = 3.3 A	$I_{\rm C} = 4A$ $I_{\rm C} = 10A$	(see Notes 5 and 6)			1.1 3	V
$V_{BE}$	Base-emitter voltage	V <sub>CE</sub> = 4 V	$I_{\rm C} = 4$ A	(see Notes 5 and 6)			1.8	V
h <sub>fe</sub>	Small signal forward current transfer ratio	V <sub>CE</sub> = 10 V	l <sub>C</sub> = 0.5 A	f = 1 kHz	15			
h <sub>fe</sub>	Small signal forward current transfer ratio	V <sub>CE</sub> = 10 V	I <sub>C</sub> = 0.5 A	f = 1 MHz	3			

NOTES: 5. These parameters must be measured using pulse techniques,  $t_p = 300 \ \mu s$ , duty cycle  $\leq 2\%$ .

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

#### thermal characteristics

PARAMETER			ТҮР	MAX	UNIT
$R_{\thetaJC}$	Junction to case thermal resistance			1.39	°C/W
$R_{\thetaJA}$	Junction to free air thermal resistance			35.7	°C/W

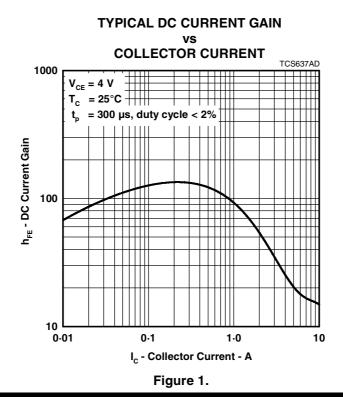
#### resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS <sup>†</sup>			MIN	ТҮР	MAX	UNIT
t <sub>on</sub> Turn-on time	I <sub>C</sub> = 6 A	$I_{B(on)} = 0.6 A$	$I_{B(off)} = -0.6 A$		0.6		μs
t <sub>off</sub> Turn-off time	$V_{BE(off)} = -4 V$	$R_L = 5 \Omega$	$t_p$ = 20 µs, dc $\leq$ 2%		1		μs

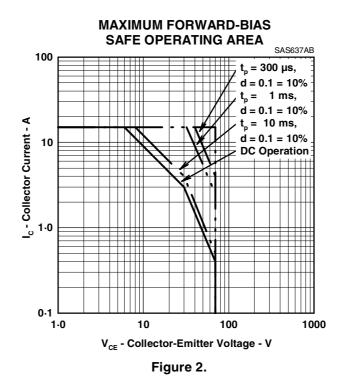
<sup>†</sup> Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.



## **TYPICAL CHARACTERISTICS**









DECEMBER 1970 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.

# THERMAL INFORMATION

